

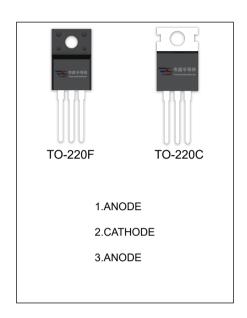
SBD30100CT、SBDF30100CT SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

Io	30 (2×15) A
V_{RRM}	100 V
T _j	150 ℃
$V_{F(typ)}$	0.70V (@Tj=125℃)

FEATURES

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Cymphol	Parameter	SBD		Heit	
Symbol	Parameter		F30100CT	Unit	
V _{RRM}	Peak repetitive reverse voltage	100		V	
V_{RWM}	Working peak reverse voltage				
V_R	DC blocking voltage				
V _{R(RMS)}	RMS reverse voltage	70		V	
Io	Average rectified output current	30		Α	
I _{FSM}	Non-Repetitive peak forward surge current (8.3ms half sine wave)	200		Α	
R _{⊙Jc}	Thermal resistance from junction to case ,Tc=25℃	2.0	3.0	°C/W	
R _{OJA}	Thermal resistance from junction to ambient	62.5		°C/W	
T _j	Junction temperature	150		$^{\circ}$	
T _{stg}	Storage temperature	-55~+150		$^{\circ}$	

ELECTRICAL CHARACTERISTICS (T₂=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Reverse voltage	V _(BR)			100			V
Reverse current	I _R	V _R =100V	Tj =25℃		5.0	100	uA
			Tj =125℃		5.0		mA
Forward voltage	V _F	I _F =10A	Tj =25℃		0.77		V
			Tj =125℃		0.64		V
		I _F =15A	Tj =25℃		0.82	0.92	V
			Tj =125℃		0.70		V

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



